

N-Ch and P-Ch Power MOSFET

GENERAL DESCRIPTION

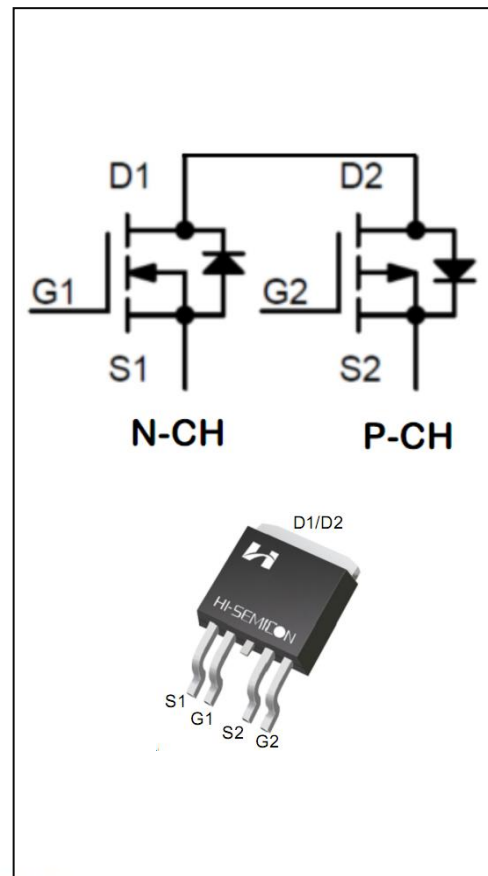
Complementary Enhancement MOSFET in a TO-252-4L Package. The SFQ0322T4 uses advanced technology and design to provide excellent $R_{DS(on)}$ with low gate charge can be used in a wide variety of applications.

Features

- ◆ N-CHANNEL
 $V_{DS}=30V, I_D=32A$
 $R_{DS(on)(TYP)}=8.0m\Omega; (V_{GS}=10V, I_D=11A)$
 $R_{DS(on)(TYP)}=11.2m\Omega; (V_{GS}=4.5V, I_D=11A)$
- ◆ P-CHANNEL
 $V_{DS}=-30V, I_D=-26A$
 $R_{DS(on)(TYP)}=10.5m\Omega; (V_{GS}=-10V, I_D=-11A)$
 $R_{DS(on)(TYP)}=14.5m\Omega; (V_{GS}=-4.5V, I_D=-11A)$

Applications

- ◆ Power factor correction (PFC)
- ◆ Switched mode power supplies (SMPS)
- ◆ Uninterruptible power supply (UPS)
- ◆ LED lighting power



ORDERING INFORMATION

Part No.	Package	Marking	Material	Packing
SFQ0322T4	T0-252-4L	SFQ0322T4	Pb Free	Reel

ABSOLUTE MAXIMUM RATINGS (T_J=25°C unless otherwise noted)

Characteristics		Symbol	N-CHANNEL	P-CHANNEL	Unit
Drain-Source Voltage		V _{DS}	30	-30	V
Gate-Source Voltage		V _{GS}	±20	±20	V
Drain Current	T _C = 25°C	I _D	32	-26	A
	T _C = 100°C		24	-19.5	
Drain Current Pulsed(Note 1)		I _{DM}	108	-88	A
Power Dissipation(T _C =25°C)		P _D	38		W
Operation Junction Temperature Range		T _J	-55 to +150		°C
Storage Temperature Range		T _{stg}	-55 to +150		°C
Maximum lead temperature for soldering purposes, 1/8" from case for 5 seconds		TL	300		°C

THERMAL CHARACTERISTICS

Characteristics	Symbol	MAX	Unit
Thermal Resistance, Junction-to-Case	R _{θJC}	3.65	°C/W
Thermal Resistance, Junction-to-Ambient	R _{θJA}	62.5	°C/W

N-Ch ELECTRICAL CHARACTERISTICS

Characteristics	Symbol	Test conditions	Min.	Typ.	Max.	Unit
Off Characteristics						
Drain -Source Breakdown Voltage	B _{VDS}	V _{GS} =0V, I _D =250μA	30		--	V
Drain-Source Leakage Current	I _{DSS}	V _{DS} =30V, V _{GS} =0V	--	--	100	nA
Gate-Source Leakage Current	I _{GSS}	V _{GS} =20V, V _{DS} =0V	--	--	100	
Gate-Source Leakage Current	I _{GSS}	V _{GS} =-20V, V _{DS} =0V	--	--	-100	
On Characteristics						
Gate Threshold Voltage	V _{GS(th)}	V _{GS} = V _{DS} , I _D =250μA	1	1.8	2.5	V
Static Drain- Source On State Resistance	R _{DS(on)}	V _{GS} =10V, I _D =11A	--	8.0	10	mΩ
		V _{GS} =4.5V, I _D =11A	--	11.2	15	mΩ
Forward Transconductance	g _{FS}	V _{DS} =10V, I _D =10A	--	13	--	S
Dynamic Characteristics						
Input Capacitance	C _{iss}	V _{DS} =15V V _{GS} =0V f=1.0MHZ	--	1610	--	pF
Output Capacitance	C _{oss}		--	185	--	
Reverse Transfer Capacitance	C _{rss}		--	126	--	
Switching Characteristics						
Turn-on Delay Time	t _{d(on)}	V _{DD} =15V; V _{GS} =10V R _G =3Ω ; I _D =10A (Note 2.3)	--	4.7	--	nS
Turn-on Rise Time	t _r		--	26.2	--	
Turn-off Delay Time	t _{d(off)}		--	42.6	--	
Turn-off Fall Time	t _f		--	15.1	--	
Total Gate Charge	Q _g	V _{DS} =15V, I _D =10A V _{GS} =10V (Note 2.3)	--	22.4	--	nC
Gate-Source Charge	Q _{gs}		--	2.3	--	
Gate-Drain Charge	Q _{gd}		--	9.9	--	

SOURCE-DRAIN DIODE RATINGS AND CHARACTERISTICS

Characteristics	Symbol	Test conditions	Min.	Typ.	Max.	Unit
Continuous Source Current	I_S	Integral Reverse P-N Junction Diode in the MOSFET	--	--	32	A
Pulsed Source Current	I_{SM}		--	--	108	
Diode Forward Voltage	V_{SD}	$I_S=20A, V_{GS}=0V$	--	0.93	1.4	V

NOTE:

- 1.Pulse width limited by maximum junction temperature
- 2.Pulse Test: Pulse width $\leq 300\mu s$, Duty cycle $\leq 2\%$
- 3.Essentially independent of operating temperature

P-Ch ELECTRICAL CHARACTERISTICS

Characteristics	Symbol	Test conditions	Min.	Typ.	Max.	Unit
Off Characteristics						
Drain -Source Breakdown Voltage	B_{VDSS}	$V_{GS}=0V, I_D=-250\mu A$	-30	--	--	V
Drain-Source Leakage Current	I_{DSS}	$V_{DS}=-30V, V_{GS}=0V$	--	--	100	nA
Gate-Source Leakage Current	I_{GSS}	$V_{GS}=20V, V_{DS}=0V$	--	--	100	nA
Gate-Source Leakage Current	I_{GSS}	$V_{GS}=-20V, V_{DS}=0V$	--	--	-100	nA
On Characteristics						
Gate Threshold Voltage	$V_{GS(th)}$	$V_{GS}=V_{DS}, I_D=-250\mu A$	-1.0	-1.5	-2.5	V
Static Drain- Source On State Resistance	$R_{DS(on)}$	$V_{GS}=-10V, I_D=-11A$	--	10.5	15	m Ω
		$V_{GS}=-4.5V, I_D=-11A$	--	14.5	25	m Ω
Forward Transconductance	g_{FS}	$V_{DS}=-10V, I_D=-10A$	--	18	--	S
Dynamic Characteristics						
Input Capacitance	C_{iss}	$V_{DS}=-15V$ $V_{GS}=0V$ $f=1.0MHZ$	--	1810	--	pF
Output Capacitance	C_{oss}		--	220	--	
Reverse Transfer Capacitance	C_{rss}		--	167	--	
Switching Characteristics						
Turn-on Delay Time	$t_{d(on)}$	$V_{DD}=15V; V_{GS}=10V$ $R_G=3\Omega; I_D=10A$ (Note 2.3)	--	9.6	--	nS
Turn-on Rise Time	t_r		--	8.3	--	
Turn-off Delay Time	$t_{d(off)}$		--	28	--	
Turn-off Fall Time	t_f		--	9.1	--	
Total Gate Charge	Q_g	$V_{DS}=-15V, I_D=-10A$ $V_{GS}=-10V$ (Note 2.3)	--	26.2	--	nC
Gate-Source Charge	Q_{gs}		--	3.8	--	
Gate-Drain Charge	Q_{gd}		--	6.1	--	

SOURCE-DRAIN DIODE RATINGS AND CHARACTERISTICS

Characteristics	Symbol	Test conditions	Min.	Typ.	Max.	Unit
Continuous Source Current	I_S	Integral Reverse P-N Junction Diode in the MOSFET	--	--	-26	A
Pulsed Source Current	I_{SM}		--	--	-88	
Diode Forward Voltage	V_{SD}	$I_S=-20A, V_{GS}=0V$	--	-0.9	-1.4	V

NOTE:

1. Pulse width limited by maximum junction temperature
2. Pulse Test: Pulse width $\leq 300\mu s$, Duty cycle $\leq 2\%$
3. Essentially independent of operating temperature

N-Channel Typical Performance Characteristics

Figure 1. On-Region Characteristics

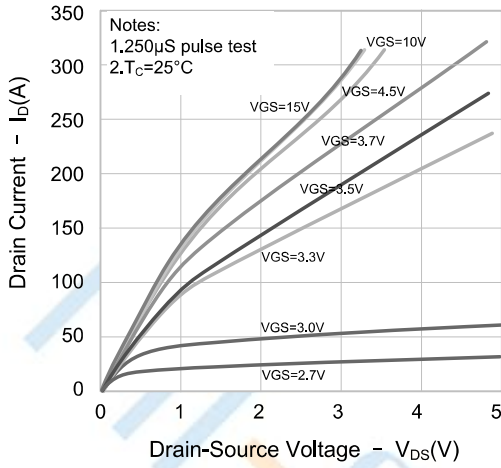


Figure 2. Transfer Characteristics

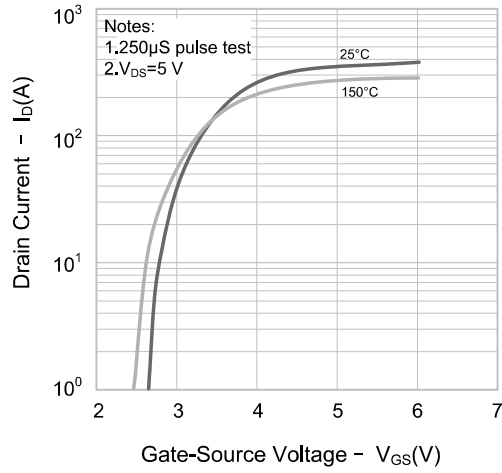


Figure 3. On-Resistance Variation vs. Drain Current

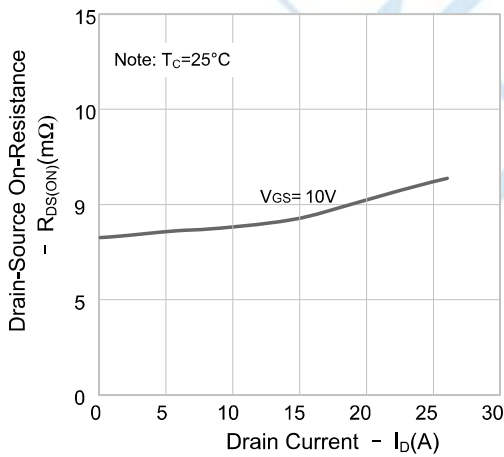


Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperature

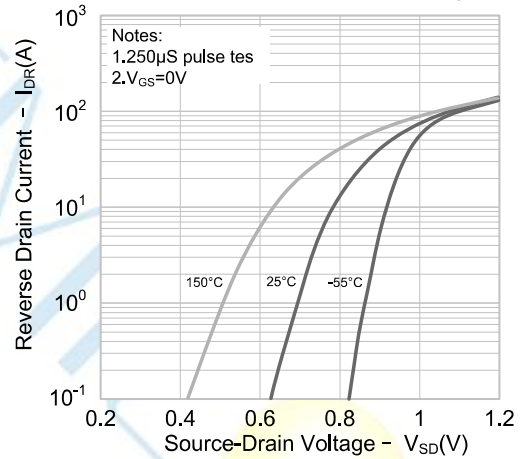


Figure 5. Capacitance Characteristics

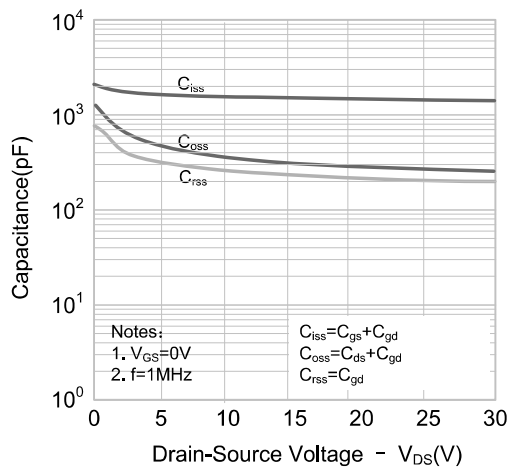
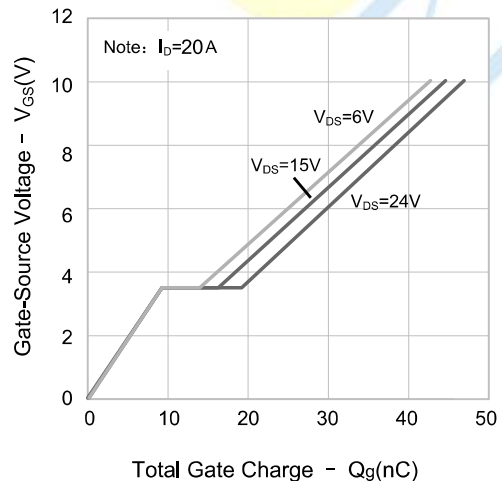


Figure 6. Gate Charge Characteristics



N-Channel Typical Performance Characteristics

Figure 7. Breakdown Voltage Variation vs Temperature

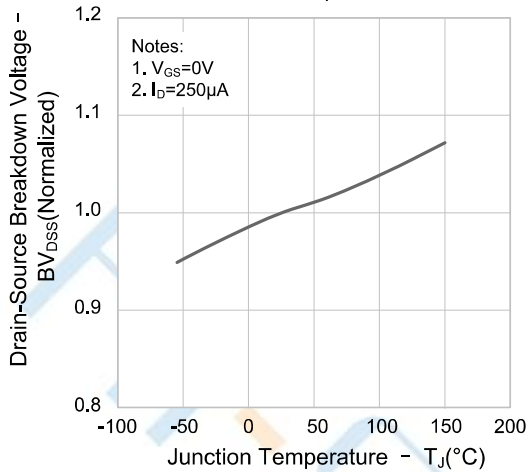


Figure 8. On-resistance Variation vs Temperature

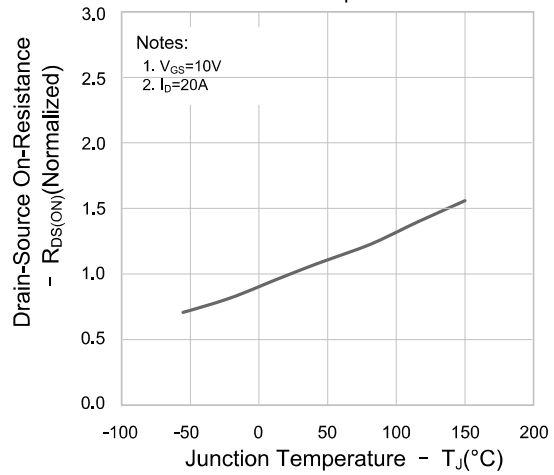
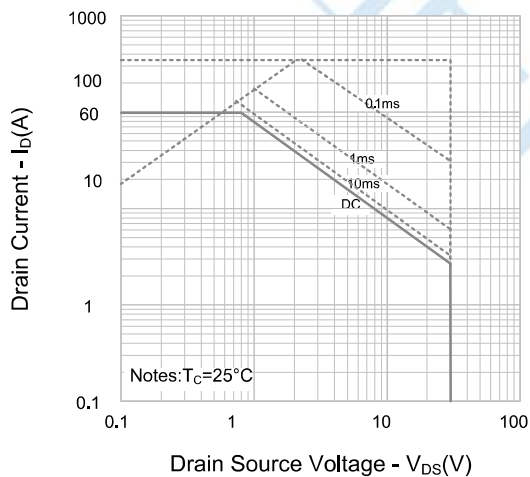


Figure 9. Max. Safe Operating Area



P-Channel Typical Performance Characteristics

Figure 1. On-Region Characteristics

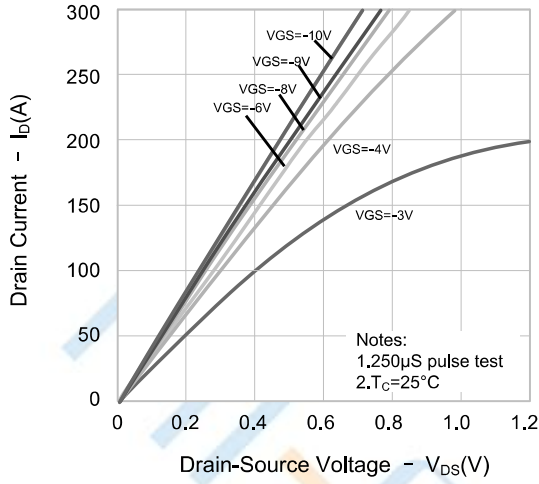


Figure 2. Transfer Characteristics

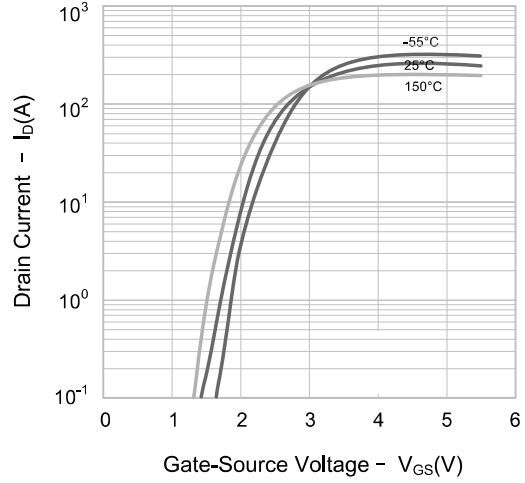


Figure 3. On-Resistance Variation vs. Drain Current

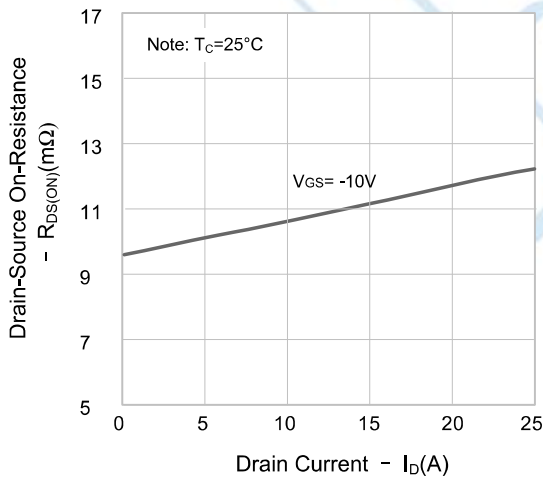


Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperature

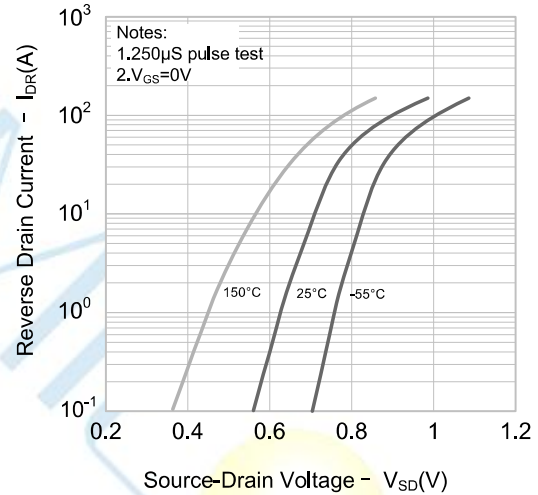


Figure 5. Capacitance Characteristics

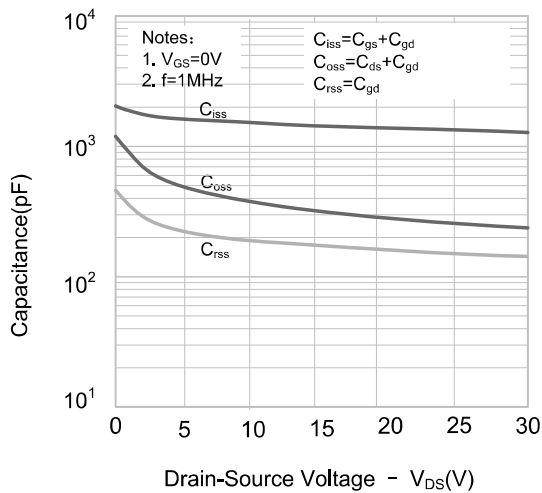
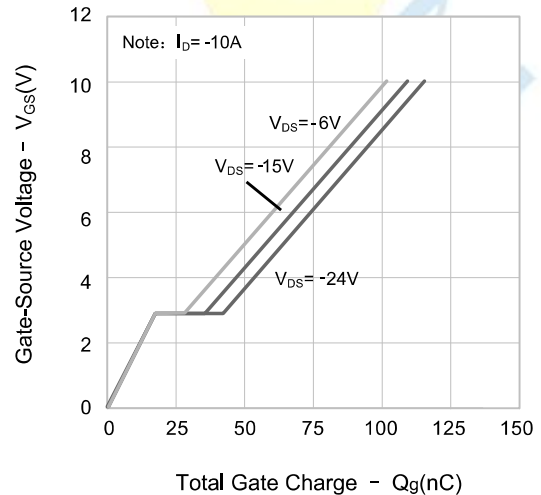


Figure 6. Gate Charge Characteristics



P-Channel Typical Performance Characteristics

Figure 7. Breakdown Voltage Variation vs Temperature

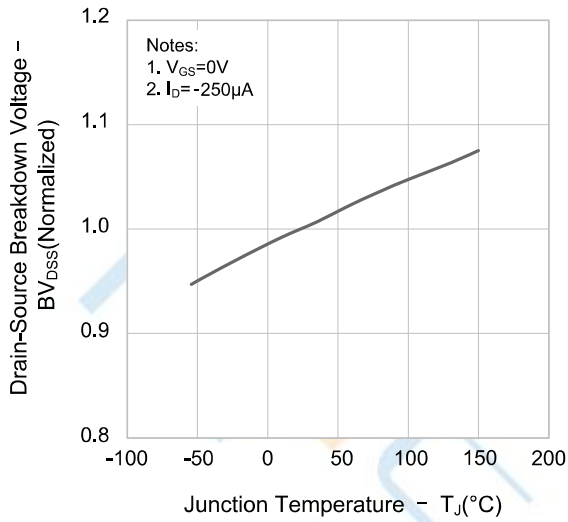


Figure 8. On-resistance Variation vs Temperature

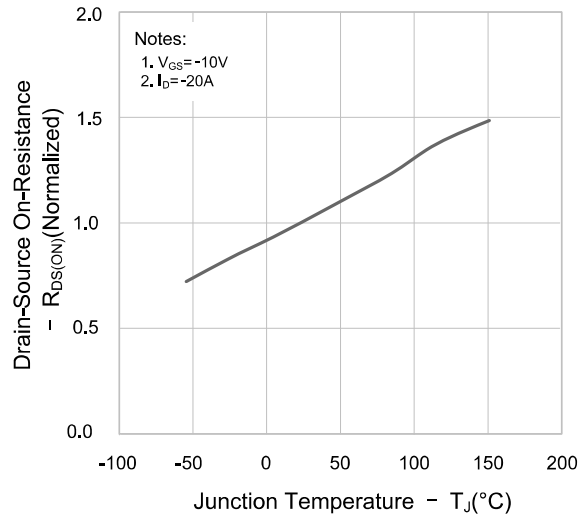
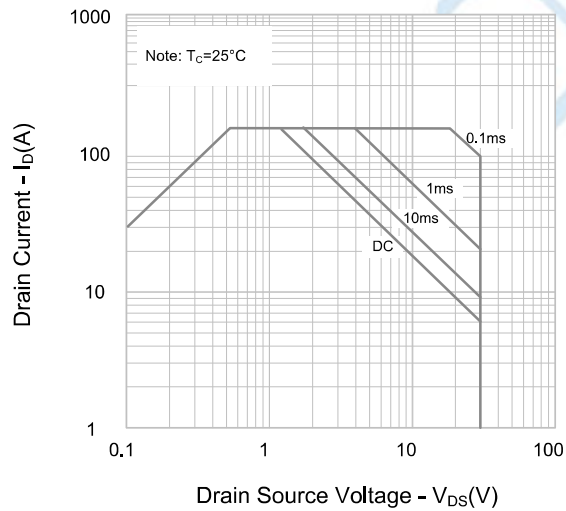
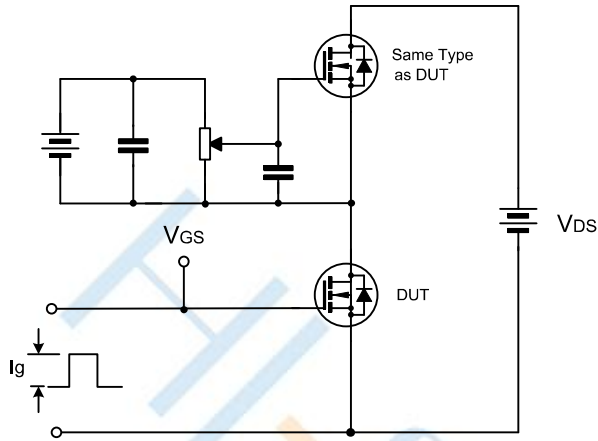


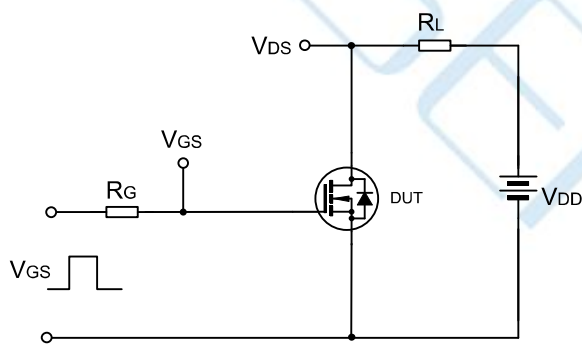
Figure 9. Max. Safe Operating Area



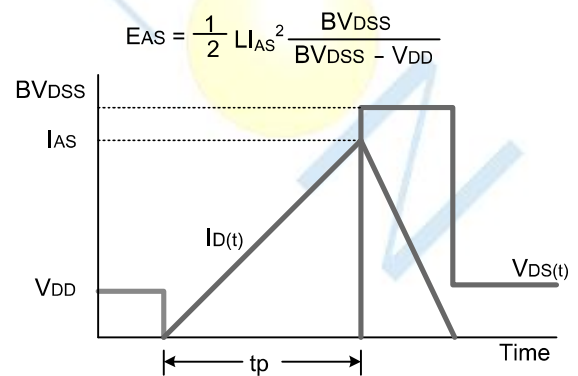
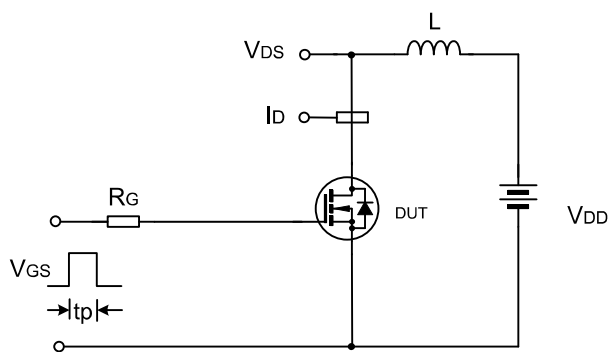
Test Circuit



Gate Charge Test Circuit & Waveform



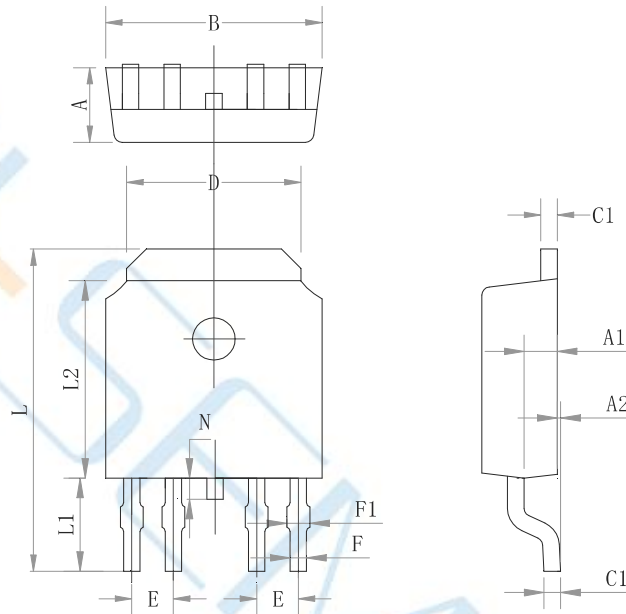
Resistive Switching Test Circuit & Waveform



EAS Test Circuit & Waveform

Package Dimensions of TO-252-4L

Unit:mm



Symbol	Min	Typ	Max
A	2.22	2.30	2.38
A1	0.93	1.01	1.08
A2	0.05	0.15	0.20
B	6.52	6.60	6.68
C	0.48	0.50	0.54
C1	0.48	0.50	0.54
D	5.22	5.32	5.42
E	1.27 TYP		
F	0.40	0.50	0.60
F1	0.50	0.60	0.70
L	9.77	9.97	10.17
L1	2.67	2.87	3.07
L2	6.02	6.10	6.18
N	0.55	0.65	0.75

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